

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1535	(438/745).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/03 19:12
L2	221	(438/747).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/03 19:13
L3	309	(257/e21.553).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/03 19:13
S1	19464	groove and wafer and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/03 16:02
S2	1159	etch\$3 near groove and wafer and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/27 13:42
S3	4727	etch\$3 with groove and wafer and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/27 13:42
S4	346	wet adj etch\$3 with groove and wafer and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/27 13:44
S5	559	wet adj etch\$3 with groove and wafer and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 13:46

EAST Search History

S6	175	wet adj etch\$3 with groove and wafer and semiconductor and spin\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 03:43
S7	26	wet adj etch\$3 with groove and wafer and semiconductor and spin\$4 and foreign	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 13:48
S8	28	wet adj etch\$3 with groove and wafer and semiconductor and spin\$4 and particles	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 13:47
S9	1	wet adj etch\$3 with groove and wafer and semiconductor and spin\$4 and round with corners	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 13:48
S10	4	wet adj etch\$3 with groove and wafer and semiconductor and spin\$4 and round\$3 with corner	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 13:48
S11	1	wet adj etch\$3 with groove and wafer and semiconductor and spin\$4 and rounding with corner	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 03:45
S12	4	wet adj etch\$3 with groove and wafer and semiconductor and spin\$4 and rounding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 03:47
S13	23	support with substrate and wet adj etch\$3 with groove and wafer and semiconductor and spin\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 03:52

EAST Search History

S14	41	support with substrate and wet with etch\$3 with groove and wafer and semiconductor and spin\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 03:48
S15	74	support with substrate and wet with etch\$3 same groove and wafer and semiconductor and spin\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 03:48
S16	1	support with substrate and wet adj etch\$3 with groove and wafer and semiconductor and rounding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 03:52
S17	23	support with substrate and wet adj etch\$3 with groove and wafer and semiconductor and round\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 03:52
S18	5963	groove same etch\$3 and wafer and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:22
S19	1159	groove near etch\$3 and wafer and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:22
S20	25	groove near etch\$3 same round\$3 and wafer and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:41
S21	3	groove near etch\$3 same round\$3 and wafer and semiconductor and support\$3 with substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:30

EAST Search History

S22	10	groove near etch\$3 same round\$3 and wafer and semiconductor and wet with etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:32
S23	1	groove near wet near etch\$3 same round\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:42
S24	7	trench near wet near etch\$3 same round\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:44
S25	0	trench near wet near etch\$3 same round\$3 and support with substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:45
S26	6	trench with wet near etch\$3 same round\$3 and support with substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:53
S27	7	(trench or groove) with wet near etch\$3 same round\$3 and support with substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:54
S28	4	(trench or groove) and wet near etch\$3 with round\$3 and support with substrate and damage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:56
S29	82	wet near etch\$3 with round\$3 and damage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:57

EAST Search History

S30	92	wet near etch\$3 with round\$3 and removal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:02
S31	63	wet near etch\$3 with round\$3 and spin\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:03
S32	1	wet near etch\$3 with round\$3 and spin\$4 same revers\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:03
S33	186	wet near etch\$3 and spin\$4 same revers\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:04
S34	104	wet near etch\$3 and spin\$4 same revers\$3 and removal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:04
S35	1	wet near etch\$3 and spin\$4 same revers\$3 and damage with removal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:05
S36	6	wet near etch\$3 and spin\$4 same revers\$3 and residue with removal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:08
S37	10	wet with etch\$3 and spin\$4 same revers\$3 and residue with removal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:08

EAST Search History

S38	153	wet with etch\$3 and spin\$4 same revers\$3 and removal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:08
S39	3	wet with etch\$3 and spin\$4 near revers\$3 and removal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:10
S40	1	wet with etch\$3 same spin\$4 near revers\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:54
S41	1207	(438/745).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/03 19:12
S42	206	(438/747).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/03 19:12
S43	244	microbalance and heater	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 15:12
S44	77	microbalance and heater and organic and detection	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 15:15
S45	63	microbalance and heater and organic and detection and substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 15:15

EAST Search History

S46	679757	thinning with substrate same groove and wet etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/27 15:26
S47	34	thinning with substrate same groove and wet etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/05/27 15:26
S48	551017	corner rounding with etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/16 18:51
S49	178	corner rounding with etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/11/16 18:51
S50	0	corner rounding with etch\$3 with groove	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/11/16 18:52
S51	61	trench with corner rounding with etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/11/16 18:52
S52	0	trench with corner rounding with etch\$3 with known	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/11/16 18:52
S53	3	trench with corner rounding with etch\$3 same known	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/11/16 18:55

EAST Search History

S54	16	semiconductor with corner rounding with etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/11/16 18:58
S55	1	semiconductor wafer with corner rounding with etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/11/16 19:18
S56	2	semiconductor wafer with corner rounding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/11/16 19:19
S57	25	wafer with corner rounding and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/11/16 19:28
S58	30	semiconductor wafer with (groove or trench) and (groove or trench) with corner round\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/18 22:58
S59	30	semiconductor wafer with (groove or trench) and (groove or trench) with corner round\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/18 23:37
S60	42	semiconductor wafer same (groove or trench) and (groove or trench) with corner round\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/18 23:25
S61	6	semiconductor wafer same (groove or trench) and (groove or trench) with corner round\$3 same wet with etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/18 23:26

EAST Search History

S62	21	"6150234"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/18 23:37
S63	3263	groove same etch\$3 and wafer and semiconductor and bond\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/03 16:03
S64	38	groove same etch\$3 and wafer and semiconductor and bond\$3 and corner with round\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/03 16:14
S65	81	groove same etch\$3 and wafer and semiconductor and bond\$3 and (corner or edge)with round\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/03 16:14
S66	15	groove same etch\$3 and wafer and semiconductor and bond\$3 and (corner or edge)with round\$3 same (wet with etch\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/03 17:39
S67	2	("20020013061").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/03 17:53
S68	84	glass substrate same bonding same semiconductor wafer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/03 17:55
S69	21	glass substrate same bonding same semiconductor wafer and wiring	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/03 18:42

EAST Search History

S70	109	spinning same HF same etch\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/03 18:43
S71	1013	spin\$4 same HF same etch\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/03 18:43
S72	5	spin\$4 same HF same etch\$3 same (corner or edge) with round\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/03 18:44
S73	21	spin\$4 same HF same etch\$3 same revers\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/03 18:46
S74	3	spin\$4 with etch\$3 same HF same revers\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/03 18:47
S75	345	spin\$4 with etch\$3 same HF	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/03 18:47
S76	22	spin\$4 with etch\$3 same HF and trench and semiconductor wafer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/03 18:48

EAST Search History

S77	6	spin\$4 with etch\$3 same HF and trench and semiconductor wafer and revers\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/03 18:48
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